

Field Effect Transistor**Silicon N Channel MOS Type (L²-π-MOS III)****High Speed, High Current DC-DC Converter,****Relay Drive and Motor Drive Applications****Features**

- 4-Volt Gate Drive
- Low Drain-Source ON Resistance
 - $R_{DS(ON)} = 0.4\Omega$ (Typ.)
- High Forward Transfer Admittance
 - $|Y_{fs}| = 0.75S$ (Typ.)
- Low Leakage Current
 - $I_{GSS} = \pm 3\mu A$ (Max.) @ $V_{GS} = \pm 16V$
 - $I_{DSS} = 100\mu A$ (Max.) @ $V_{DS} = 60V$
- Enhancement-Mode
 - $V_{th} = -0.8 \sim -2.0V$ @ $V_{DS} = 10V, I_D = 1mA$

Absolute Maximum Ratings (Ta = 25°C)

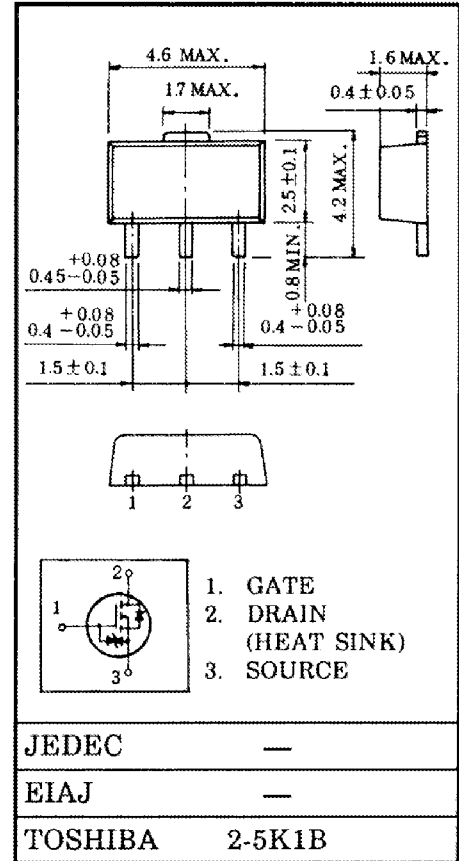
CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	0.8	A
	Pulse	I_{DP}	2.4	
Drain Power Dissipation (Ta = 25°C)		P_D	0.5	W
Drain Power Dissipation		P_D^*	1.0	W
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	-55 ~ 150	°C

P_D^* : 2SK1078 mounted on ceramic substrate (250 mm² x 0.8t)

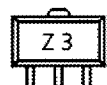
Thermal Characteristics

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	250	°C/W

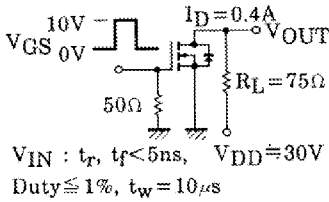
This transistor is an electrostatic sensitive device. Please handle with care.

Industrial Applications Unit in mm

Weight : 0.05g

Marking

Electrical Characteristics (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$	-	-	± 10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$	-	-	100	μA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10mA, V_{GS} = 0V$	60	-	-	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V, I_D = -1mA$	0.8	-	-2.0	V
ON State Drain Current		$I_D(ON)$	$V_{DS} = 4V, V_{GS} = 4V$	0.8	-	-	A
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 4V, I_{DS} = 0.4A$	-	0.75	1.1	Ω
			$V_{GS} = 10V, I_{DS} = 0.4A$	-	0.40	0.55	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10V, I_{DS} = 0.4A$	0.50	0.75	-	S
Input Capacitance		C_{iss}	$V_{DS} = 10V, V_{GS} = 0V,$ $f = 1MHz$	-	95	140	μF
Reverse Transfer Capacitance		C_{rss}		-	25	50	
Output Capacitance		C_{oss}		-	60	110	
Switching Time	Rise Time	t_r	 <p>$V_{GS} = 10V, 0V$ $I_D = 0.4A$ $R_L = 75\Omega$ $V_{IN} : t_r, t_f < 5ns, V_{DD} \approx 30V$ Duty $\leq 1\%, t_w = 10\mu s$</p>	-	4	15	ns
	Turn-on Time	t_{on}		-	9	25	
	Fall Time	t_f		-	25	60	
	Turn-off Time	t_{off}		-	55	120	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} = 48V, V_{GS} = 10V,$ $I_D = 0.8A$	-	5.2	10	nC
Gate-Source Charge		Q_{gs}		-	3.5	-	
Gate-Drain ("Miller") Charge		Q_{gd}		-	1.7	-	

Source-Drain Diode Ratings and Characteristics (Ta = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	-	-	-	0.8	A
Pulse Drain Reverse Current	I_{DRP}	-	-	-	2.4	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 0.8A, V_{GS} = 0V$	-	-0.9	-1.5	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 0.8A, V_{GS} = 0V$	-	90	-	ns
Reverse Recovered Charge	Q_{rr-}	$dI_{DR}/dt = 20A/\mu s$	-	35	-	nC

